

Notice of References Cited

Application/Control No.

09/680,054

Applicant(s)/Patent Under
Reexamination
NAKAMURA ET AL.

Examiner

Brook Kebede

Art Unit

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	V	Yu et al., Study of the epitaxial-lateral-overgrowth (ELO) process for GaN on sapphire, Journal of Crystal Growth, 195 pp 333-339 (1998).
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Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.